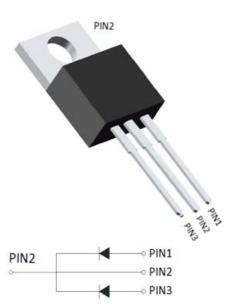
MBRL20120CT



Schottky Diodes



Features

- High frequency operation
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Guard ring for enhanced ruggedness and long term reliability
- Solder dip 275 °C max. 7 s, per JESD 22-B106

Typical Applications

Typical applications are in switching power supplies, converters, freewheeling diodes, and reverse battery protection.

Mechanical Data

• Package: TO-220AB

Molding compound meets UL 94 V-0 flammability

rating, RoHS-compliant

• Terminals: Tin plated leads, solderable per

J-STD-002 and JESD22-B102

• Polarity: As marked

■Maximum Ratings (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	MBRL20120CT
Device marking code			MBRL20120CT
Repetitive Peak Reverse Voltage	V_{RRM}	V	120
Average Rectified Output Current @60Hz sine wave, R-load, Tc=116℃	Io	А	20
Surge(Non-repetitive)Forward Current @60Hz half sine-wave, 1 cycle, Ta=25 ℃	I _{FSM}	А	200
Current Squared Time @1ms≤t≤8.3ms Tj=25°C	l²t	A ² s	166
Storage Temperature	T_{stg}	$^{\circ}$	-55 ~ + 150
Junction Temperature	Tj	°C	-55 ~ + 150

■Electrical Characteristics (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	MBRL20120CT
Maximum instantaneous forward voltage drop per diode	V_{FM}	V	I _{FM} =10.0A	0.85
Maximum DC reverse current at rated	I _{RRM1}	mA	V _{RM} =V _{RRM} Ta=25℃	0.1
DC blocking voltage per diode	I _{RRM2}		V _{RM} =V _{RRM} Ta=100°C	20

Note1:Pulse test:300uS pulse widh,1% duty cycle

Note2:Pulse test:pulse widh 40mS

MBRL20120CT

PARAMETER		SYMBOL	UNIT	MBRL20120CT
Thermal Resistance	Between junction and case	R _{θJ-C}	°C/W	2.0

■Ordering Information (Example)

PREFERED P/	N UNIT WEIGHT(g)	MINIIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
MBRL20120C	T Approximate 1.9	50	1000	5000	Tube

■Characteristics (Typical)

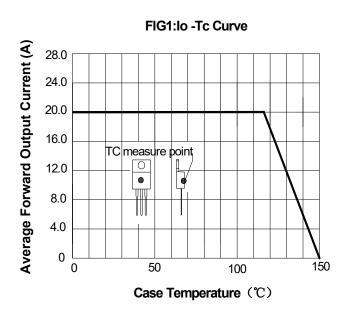
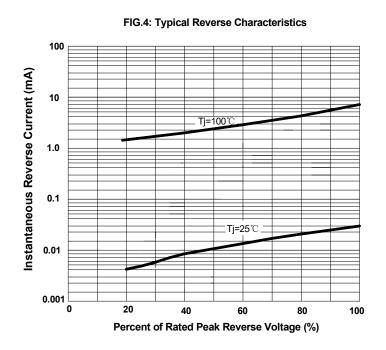


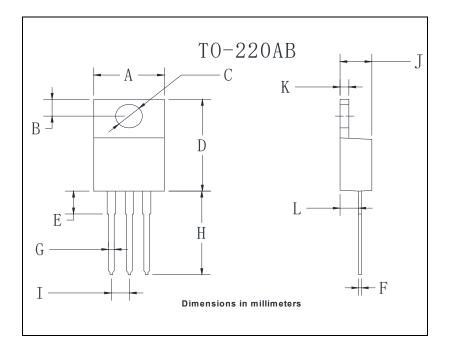
FIG2:Surge Forward Current Capability 300 Peak Forward Surge Current (A) 250 200 8.3ms Single Half Sine-Wave 150 JEDEC Method 100 50 0 2 5 10 20 50 100 **Number of Cycles**







■Outline Dimensions



TO-220AB					
Dim	Min	Max			
Α	9.95	10.35			
В	2.55	2.95			
С	3.8	4.0			
D	14.95	15.25			
E	3.75	4.25			
F	0.26	0.5			
G	0.68	0.94			
Н	13.4	13.9			
I	2.35	2.65			
J	4.38	4.78			
K	1.14	1.4			
L	2.37	2.79			



MBRL20120CT

Disclaimer

The information presented in this document is for reference only. Yangzhou Yangjie Electronic Technology Co., Ltd. reserves the right to make changes without notice for the specification of the products displayed herein to improve reliability, function or design or otherwise.

The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used with equipment or devices which require high level of reliability and the malfunction of with would directly endanger human life (such as medical instruments, transportation equipment, aerospace machinery, nuclear-reactor controllers, fuel controllers and other safety devices), Yangjie or anyone on its behalf, assumes no responsibility or liability for any damages resulting from such improper use of sale.

This publication supersedes & replaces all information previously supplied. For additional information, please visit our website http:// www.21yangjie.com, or consult your nearest Yangjie's sales office for further assistance.